

# Table of Contents

## Acknowledgements

## Committees and Sponsors

## Photo

## Preface

## I. Physical Cleaning Methods

<b>Direct Observation of Single Bubble Cavitation Damage for MHz Cleaning</b>	
H. Tomita, M. Inukai, K. Umezawa and L.N. Ji	3
<b>High Speed Imaging of 1 MHz Driven Microbubbles in Contact with a Rigid Wall</b>	
A. Zijlstra, T. Janssens, K. Wostyn, M. Versluis, P.W. Mertens and D. Lohse	7
<b>Characterization of a Cavitation Bubble Structure at 230 kHz: Bubble Population, Sonoluminescence and Cleaning Potential</b>	
A. Otto, T. Nowak, R. Mettin, F. Holsteys and A. Lippert	11
<b>Impact of Megasonic Activation with Different Chemistries on Silicon Surface in Single Wafer Tool</b>	
G. Briand, P. Besson, T. Salvetat and S. Petitdidier	15
<b>Impacts of Ionization Potentials and Megasonic Dispersion</b>	
C. Franklin	19
<b>The Influence of Standing Waves on Cleaning with a Megasonic Nozzle</b>	
T. Janssens, G. Doumen, S. Halder, K. Wostyn, P.W. Mertens and J. Straka	23
<b>Megasonic Sweeping and Silicon Wafer Cleaning</b>	
J.M. Goodson and R. Nagarajan	27
<b>Removal of Nano-Particles by Aerosol Spray: Effect of Droplet Size and Velocity on Cleaning Performance</b>	
K. Xu, S. Pichler, K. Wostyn, G. Cado, C. Springer, G.W. Gale, M. Dalmer, P.W. Mertens, T. Bearda, E. Gaulhofer and D. Podlesnik	31
<b>High Aspect Ratio Contact Clean Study in 58nm Flash Device</b>	
P.C. Yu, C.K. Chen, J.L. Lin, C.N. Wu and H. Matsuo	35
<b>High Velocity Aerosol Cleaning with Organic Solvents: Particle Removal and Substrate Damage</b>	
M.T. Andreas, K. Wostyn, M. Wada, T. Janssens, K. Kenis, T. Bearda and P.W. Mertens	39
<b>Cleaning Technique Using High-Speed Steam-Water Mixed Spray</b>	
M. Watanabe, T. Sanada, A. Hayashida and Y. Isago	43
<b>Pattern Collapse and Particle Removal Forces of Interest to Semiconductor Fabrication Process</b>	
T.G. Kim, K. Wostyn, J.G. Park, P.W. Mertens and A.A. Busnaina	47
<b>Applications of Electrostatic Spray Techniques to Surface Cleaning</b>	
K. Finster, R. Small, A. Belz, J. Mahoney, J. Perel and J. Gong	51
<b>Analyzing the Collapse Force of Narrow Lines Measured by Lateral Force AFM Using an Analytical Mechanical Model</b>	
K. Wostyn, T.G. Kim, P.W. Mertens and J.G. Park	55

## II. Particle Interactions

<b>Reduced Particle Removal Efficiency Upon Wafer Storage</b>	
D.M. Knotter, R. Roucou and R. Peyrin	61
<b>Local Distribution of Particles Deposited on Patterned Surfaces</b>	
F. Wali, D.M. Knotter, T. Bearda and P.W. Mertens	65
<b>Particle Retention Mechanism of Filter in High Temperature Chemical</b>	
T. Nagafuchi, K. Chiba, I. Funahashi, M. Inukai, H. Yamada, K. Umezawa and H. Tomita	69

## **Improving Process Control for Copper Electroplating through Filter Membrane Optimization**

A.W. Wu, G. Cornner and V. Prabhaker 73

## **Particle – Wafer Interactions in Semiaqueous Silicon Cleaning Systems**

L. Hupka, J. Nalaskowski, N. Sinha, J.N. Greeley, Z. Clark, H. Du, W.P. Johnson and J.D. Miller 77

## **III. Drying**

### **Drying of High Aspect Ratio Structures: A Comparison of Drying Techniques via Electrical Stiction Analysis**

A. Pacco, M. Wada, T. Bearda and P.W. Mertens 87

### **Relationship between Atmospheric Humidity and Watermark Formation in IPA Dry of Si Wafer after HF Clean**

N. Kurumoto, A. Eitoku and K. Miya 91

## **IV. Metrology**

### **Complementary Metrology within a European Joint Laboratory**

A. Nutsch, B. Beckhoff, R. Altmann, J.A. Van den Berg, D. Giubertoni, P. Hönicke, M. Bersani, A. Leibold, F. Meirer, M. Müller, G. Pepponi, M. Otto, P. Petrik, M. Reading, L. Pfitzner and H. Ryssel 97

### **Highly Sensitive Detection of Inorganic Contamination**

B. Beckhoff, A. Nutsch, R. Altmann, G. Borionetti, C. Pello, M.L. Polignano, D. Codegoni, S. Grasso, E. Cazzini, M. Bersani, P. Lazzeri, S. Gennaro, M. Kolbe, M. Müller, P. Kregsamer and F. Posch 101

### **Trace Metallic Contamination Analysis on Wafer Edge and Bevel by TXRF and VPD-TXRF**

H. Takahara and K. Tsugane 105

### **Surface Potential Difference Imaging Applied to Wet Clean Monitoring**

A. Danel, S. Sage, M.C. Roure, D. Peters, J. Hawthorne and R. Spicer 109

## **V. Contamination Control**

### **Metallic Contamination Control in Leading-Edge ULSI Manufacturing**

A. Shimazaki, H. Sakurai, M. Iwase, R. Yoshimura and T. Tada 115

### **Molybdenum Contamination in Silicon: Detection and Impact on Device Performances**

D. Codegoni, M.L. Polignano, D. Caputo, A. Riva, E. Blot, D. Coulon, P. Maillot and N. Pic 123

### **Developing a High Volume Manufacturing Wet Clean Process to Remove BF<sub>2</sub> Implant Induced Molybdenum Contamination**

A. Sehgal, H.H. Huang, J. Ramdani, J. Klatt, C. Printy, S. Ruby and T. Thibeault 127

### **Impact of Metal-Ion Contaminated Silica Particles on Gate Oxide Integrity**

I. Rink, F. Wali and D.M. Knotter 131

### **Monitoring System for Airborne Molecular Contamination (AMC) in Semiconductor Manufacturing Areas and Micro-Environments**

M. Otto, A. Leibold, L. Wulf, M. Hurlebaus and L. Pfitzner 135

### **Reduction of Airborne Molecular Contamination on 300 mm Front Opening Unified POD (FOUP) and Wafers Surface by Vacuum Technology**

P. Maquin and H. Kambara 139

### **Study of the Volatile Organic Contaminants Absorption and their Reversible Outgassing by FOUPs**

H. Fontaine, S. Cetre, M. Veillerot and A. Danel 143

### **Prevention of Condensation Defects on Contact Patterns by Improving Rinse Process**

J.M. Oh, J.N. Han, K.T. Lee, C.K. Hong, W.S. Han, J.T. Moon and J.G. Park 151

### **Single Wafer Ozone-Based Processing for Effective Edge Fluoropolymer Cleaning**

J. Niccoli, M. Cogrono, M. Eastlack, D. McCane, C. Carlson, E. Young and D. Chapek 155

### **Cleanliness Management in Advanced Microelectronic**

Y. Borde, A. Danel, A. Roche, H. Fontaine and C. Brych 159

## **VI. Front End of Line: Surface Preparation and Etching**

<b>Surface Preparation and Passivation of III-V Substrates for Future Ultra-High Speed, Low Power Logic Applications</b>		
W. Rachmady, J. Blackwell, G. Dewey, M. Hudait, M. Radosavljevic, R. Turkot Jr. and R. Chau		165
<b>Preparation and Characterization of Self-Assembled Monolayers on Germanium Surfaces</b>		
M. Lommel, P. Hönicke, M. Kolbe, M. Müller, F. Reinhardt, P. Möbus, E. Mankel, B. Beckhoff and B.O. Kolbesen		169
<b>Application of Single-Wafer Wet Cleaning Prior to Epitaxial SiGe Process</b>		
K. Sano, M. Wada, F.E. Leys, R. Loo, A. Hikavyy, P.W. Mertens, J. Snow, A. Izumi, K. Miya and A. Eitoku		173
<b>Low Temperature Pre-Epi Treatment: Critical Parameters to Control Interface Contamination</b>		
R. Loo, A. Hikavyy, F.E. Leys, M. Wada, K. Sano, B. De Vos, A. Pacco, M. Bargallo Gonzalez, E. Simoen, P. Verheyen, W. Vanherle and M. Caymax		177
<b>Silicon Surface Preparation and Passivation by Vapor Phase of Heavy Water</b>		
A.E. Pap, Z. Nényei, G. Battistig and I. Bársenyi		181
<b>Defects of Silicon Substrates Caused by Electro-Static Discharge in Single Wafer Cleaning Process</b>		
Y. Hagimoto, H. Iwamoto, Y. Honbe, T. Fukunaga and H. Abe		185
<b>Three-Step Room Temperature Wet Cleaning Process for Silicon Substrate</b>		
R. Hasebe, A. Teramoto, T. Suwa, R. Kuroda, S. Sugawa and T. Ohmi		189
<b>Effect of Wet Treatment on Stability of Spin-On Dielectrics for STI Gap-Filling in Nanoscale Memory</b>		
G.H. Kim, S.Y. Park, S.S. Pyo, J.H. Han, J.N. Kim, K.J. Oh, C.K. Ryu, Y.S. Choi, N.J. Kwak and S.K. Park		193
<b>Influence of Wet Cleaning on Tungsten Deposited with Different Techniques</b>		
A. Votta, F. Pipia, S. Borsari, E. Ravizza, A.C. Elbaz, M. Alessandri, E. Bellandi and C. Bresolin		197

## **VII. Front End of Line: Etching**

<b>Etch Rate Study of Germanium, GaAs and InGaAs: A Challenge in Semiconductor Processing</b>		
S. Sioncke, D.P. Brunco, M. Meuris, O. Uwamahoro, J. Van Steenbergen, E. Vrancken and M. Heyns		203
<b>Poly-Silicon Etch with Diluted Ammonia: Application to Replacement Gate Integration Scheme</b>		
F. Sebaai, J.I. Del Agua Borniquel, R. Vos, P. Absil, T. Chiarella, C. Vrancken, P. Boelen and E. Baiya		207
<b>Advances on 45nm SiGe-Compatible NiPt Salicide Process</b>		
Y.W. Chen, N.T. Ho, J. Lai, T.C. Tsai, C.C. Huang, S.F. Tzou and J.M.M. Chu		211
<b>Impact of Galvanic Corrosion on Metal Gate Stacks</b>		
M. Wada, S. Garaud, I. Ferain, N. Collaert, K. Sano, J. Snow, R. Vos, L.H.A. Leunissens, P.W. Mertens and A. Eitoku		215
<b>Photoresist Adhesion during Wet Etch on Single Wafer Tool</b>		
P. Garnier, B. Pernet, Y. Gomez, C. Duluard, A. Torres, D. Barge, M. Gatefait and D. Lévy		219
<b>Surface Texturization and Interface Passivation of Mono-Crystalline Silicon Substrates by Wet Chemical Treatments</b>		
W. Sievert, K.U. Zimmermann, B. Hartmann, C. Klimm, K. Jacob and H. Angermann		223
<b>Mechanism of Plasma-Less Gaseous Etching Process for Damaged Oxides from the Ion Implantation Process</b>		
S. Saito, Y. Hagimoto, H. Iwamoto and Y. Muraki		227
<b>Current Advances in Anhydrous HF/Organic Solvent Processing of Semiconductor Surfaces</b>		
P. Roman, K. Torek, K. Shanmugasundaram, P. Mumbauer, D. Vestyk, P. Hammond and J. Ruzyllo		231
<b>Co-Solvent Effect on the HF/CO<sub>2</sub> Dry Etching of Sacrificial Oxides</b>		
J.H. Bae, J.M. Jung and K.T. Lim		235

## **VIII. Front End of Line: Post Ion Implantation Photo Resist Strip**

<b>Material Loss Impact on Device Performance for 32nm CMOS and Beyond</b>	245
B.K. Kirkpatrick, J.J. Chambers, S.L. Prins, D.J. Riley, W.Z. Xiong and X. Wang	
<b>Evaluation of Plasma Strip Induced Substrate Damage</b>	249
K.P. Han, S. Luo, O. Escoria, C. Waldorf and I.L. Berry	
<b>Post Extension Ion Implant Photo Resist Strip for 32 nm Technology and beyond</b>	253
G. Mannaert, L. Witters, D. Shamiryan, W. Boullart, K. Han, S. Luo, A. Falepin, R. Sonnemans, I.L. Berry and C. Waldorf	
<b>Influence of Dry Ashing and Wet Treatments on NVM Metal Gate Structures</b>	257
A.C. Elbaz, E. Bellandi, C. De Marco, L.M. Avaro, E. Ravizza, R. Piva and M. Alessandri	
<b>Chemical and Mechanical Analysis of HDIS Residues Using Auger Electron Spectroscopy and Nanoindentation</b>	261
A.V. Kadavanich, S.H. Shim, H.M. Meyer, S.E. Savas and E. Lara-Curzio	
<b>Shortening of Plasma Strip Process Resulting in Better Removal of Photo Resist after High Dose Implantation</b>	265
A. Zakharov, M. Lenski, S. Metzger and C. Krüger	
<b>Stripping and Cleaning of High-Dose Ion-Implanted Photoresists Using a Single-Wafer, Single-Chamber Dry/Wet Hybrid System</b>	269
Y.J. Kim, J.H. Lee, K.J. Seo, C.R. Yoon, E.S. Roh, J.K. Cho and T. Hattori	
<b>Post Ion-Implant Photoresist Stripping Using Steam and Water: Pre-Treatment in a Steam Atmosphere and Steam-Water Mixed Spray</b>	273
T. Sanada, M. Watanabe, A. Hayashida and Y. Isago	
<b>Steam-Injected SPM Process for All-Wet Stripping of Implanted Photoresist</b>	277
D. Dekraker, B. Pasker, J.W. Butterbaugh, K.K. Christenson and T.J. Wagener	
<b>Novel Methods for Wet Stripping High Dose Implanted Photoresist Using Sulfur Trioxide</b>	281
E.J. Bergman and J.D. Leonhard	
<b>All Wet Photoresist Strip by Solvent Aerosol Spray</b>	285
M. Wada, K. Sano, J. Snow, R. Vos, L.H.A. Leunissen, P.W. Mertens and A. Eitoku	
<b>Stripping of Ion Implanted Photoresist by CO<sub>2</sub> Cryogenic Pre-Treatment Followed by Wet Cleaning</b>	289
S. Malhouitre, R. Vos, S. Banerjee, P. Cheng, T. Bearda and P.W. Mertens	

## **IX. Back End of Line: Post Dielectric Etch Photo Resist Strip**

<b>Porous Low-k Wet Etch in HF-Based Solutions: Focus on Cleaning Process Window, "Pore-Sealing" and "k Recovery"</b>	295
L. Brousseau, W. Puyrenier, D. Rebiscoul, V. Rouessac and A. Ayral	
<b>Photoresist Removal Using Alternative Chemistries and Pressures</b>	303
I.G. Song, C. Timmons, G. Levitin and D.W. Hess	
<b>Ozone Chemistry for BEOL Resist Stripping – A Systematic Analytical Attempt to Understand the Interaction of O<sub>3</sub> with Modern DUV-Resists</b>	311
M. Guder, M. Pellowska, M. Pohland, M. Dalmer and B.O. Kolbesen	
<b>Design and Development of Novel Remover for Cu/Porous Low-k Interconnects</b>	315
T. Suzuki, A. Otake and T. Aoki	
<b>Surface Energy and Wetting Behaviour of Plasma Etched Porous SiCOH Surfaces and Plasma Etch Residue Cleaning Solutions</b>	319
N. Ahner, M. Schaller, C. Bartsch, E. Baryschpolec and S.E. Schulz	
<b>Modification of Photoresist by UV for Post-Etch Wet Strip Applications</b>	323
Q.T. Le, E. Kesters, L. Prager, M. Claes, M. Lux and G. Vereecke	
<b>Recyclable Fluorine-Based Cleaning Solvents for Resist Removal</b>	327
H. Okamoto and H. Namatsu	
<b>Cu Dendrite Formation in Post Trench Etch Cleaning</b>	331
J.S. Heo, J.H. Oh, H.J. Shin and N.I. Lee	

<b>The Interaction of Sublimed Iminodiacetic Acid with a Cu{110} Surface</b>	335
D.W. Tee, S.M. Francis, N.V. Richardson, C. Reid and L. McGhee	
<b>Advances in Test Wafer Reclaim Technology – Wet Stripping Porous Low-k Films with No Substrate Damage</b>	339
M. Robson, K.A. Fletcher, P. Jiang, M.B. Korzenski, A. Upham, T. Haigh Jr. and T.J.C. Hsieh	
<b>Electrochemical Behavior of Cobalt in Post-Via Etch Cleaning Solutions</b>	343
S. Bilouk, C. Pernel, L. Broussous, V. Ivanova and R. Nogueira	

## X. Back End of Line: Post Metal Etch Photo Resist Strip

<b>Characterization of Post Etch Residues Depending on Resist Removal Processes after Aluminum Etch</b>	349
M. Heidenblut, D. Sturm, A. Lechner and F. Faupel	
<b>Impact of Dry Etch and Ash Conditions on Removability of Plasma Etch Residues in Al-Metallization. Approach to Improve PER Cleaning Efficiency by EHS-Friendly Aqueous Remover</b>	353
B. Ferstl, A. Klipp, M. Essig and M. Heidenblut	
<b>Borderless via Clean Study for Minimizing Al-Cu Loss in 58nm Flash Devices</b>	357
C.K. Chen, P.C. Yu, M.H. Lee, C.N. Wu and H. Matsuo	

## XI. Back End of Line: Post Cu CMP Cleaning

<b>Effect of Various Cleaning Solutions and Brush Scrubber Kinematics on the Frictional Attributes of Post Copper CMP Cleaning Process</b>	363
Y. Sampurno, Y. Zhuang, X. Gu, S. Theng, T. Nemoto, T. Sun, F. Sudargho, A. Teramoto, A. Philipossian and T. Ohmi	
<b>The Effect of PVA Brush Scrubbing on Post CMP Cleaning Process for Damascene Cu Interconnection</b>	367
H.C. Cho, Y.M. Kim, H.S. Lee, S.B. Joo and H.D. Jeong	
<b>Cu Surface Characterization after Wet Cleaning Processes</b>	371
F. Pipia, A. Votta, A.C. Elbaz, S. Grasso, E. Ravizza, S. Spadoni and M. Alessandri	
<b>Impact of CMP Polish and pCMP Cleaning on Adhesion of SiCN Capping Layer on PECVD-Derived Porous OSG and Copper</b>	377
D.M. Gage, A.D.W. Thiel, R.H. Dauskardt, M.K. Haas, L.M. Matz, M.L. O'Neill, T.M. Wieder, G. Banerjee and M.B. Rao	
<b>Damage-Free Post-CMP Cleaning Solution for Low-k Fluorocarbon on Advanced Interconnects</b>	381
X. Gu, T. Nemoto, A. Teramoto, R. Hasebe, T. Ito and T. Ohmi	
<b>Process Dependence on Defectivity Count on Copper and Dielectric Surfaces in Post-Copper CMP Cleaning</b>	385
J. Daviot and J. Vaes	
<b>A Novel Copper Interconnection Cleaning by Atomic Hydrogen Using Diluted Hydrogen Gas</b>	389
K. Abe and A. Izumi	